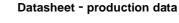
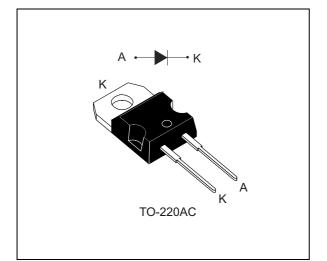


# STPSC12C065-Y

### Automotive 650 V power Schottky silicon carbide diode





### Features

- No or negligible reverse recovery
- Switching behavior independent of temperature
- Dedicated to PFC applications
- High forward surge capability
- AEC-Q101 qualified
- PPAP capable
- ECOPACK®2 compliant component

### Description

The SiC diode is an ultrahigh performance power Schottky diode. It is manufactured using a silicon carbide substrate. The wide band gap material allows the design of a Schottky diode structure with a 650 V rating. Due to the Schottky construction, no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature and is ideal for automotive applications.

Especially suited for use as boost diode, this rectifier will enhance the performance in hard switching conditions. Its high forward surge capability ensures a good robustness during transient phases.

#### Table 1. Device summary

Symbol	Value
I <sub>F(AV)</sub>	12 A
V <sub>RRM</sub>	650 V
T <sub>j</sub> (max)	175 °C

This is information on a product in full production.

#### **Characteristics** 1

#### Table 2. Absolute ratings (limiting values at 25 °C unless otherwise specified)

Symbol	Par	Value	Unit	
V <sub>RRM</sub>	Repetitive peak reverse voltage, T <sub>j</sub> = -40 °C		650	V
I <sub>F(RMS)</sub>	Forward rms current		22	А
I <sub>F(AV)</sub>	Average forward current	$T_c = 120 \ ^{\circ}C^{(1)}, \ \delta = 0.5$	12	А
I <sub>FSM</sub>	Surge non repetitive forward current	$t_p = 10$ ms sinusoidal, $T_c = 25$ °C $t_p = 10$ ms sinusoidal, $T_c = 125$ °C $t_p = 10$ µs square, $T_c = 25$ °C	92 84 470	A
I <sub>FRM</sub>	Repetitive peak forward current	$T_c = 120 \ ^{\circ}C^{(1)}, T_j = 175 \ ^{\circ}C, \delta = 0.1$	51	А
T <sub>stg</sub>	Storage temperature range		-65 to +175	°C
Тj	Operating junction temperature <sup>(2</sup>	-40 to +175	°C	

 $\begin{array}{ll} \text{1.} & \text{Value based on } \mathsf{R}_{th(j-c)} \text{ max.} \\ \text{2.} & \frac{dPtot}{dTj} < \frac{1}{\mathsf{R}th(j-a)} \text{ condition to avoid thermal runaway for a diode on its own heatsink} \end{array}$ 

#### Table 3. Thermal resistance

Symbol	Parameter	Val	Unit	
	raiameter	Тур.	Max.	onit
R <sub>th(j-c)</sub>	Junction to case	1.2	1.7	°C/W

Symbol	Parameter	Tests conditions		Min.	Тур.	Max.	Unit
I <sub>R</sub> <sup>(1)</sup>	Poverse leekage ourrent	T <sub>j</sub> = 25 °C	V _ V	-	10	120	
I <sub>R</sub> <sup>(1)</sup> Reverse leakage current	T <sub>j</sub> = 150 °C	V <sub>R</sub> = V <sub>RRM</sub>	-	100	500	μA	
V (2)	V <sub>F</sub> <sup>(2)</sup> Forward voltage drop	T <sub>j</sub> = 25 °C	I <sub>F</sub> = 12 A	-	1.56	1.75	V
۷F		T <sub>j</sub> = 150 °C	1F – 12 A	-	1.98	2.5	v

1.  $t_p = 10 \text{ ms}, \delta < 2\%$ 

2.  $t_p = 500 \ \mu s, \ \delta < 2\%$ 

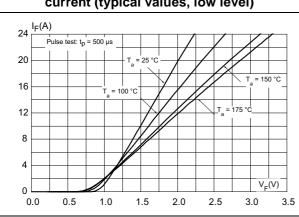
To evaluate the conduction losses use the following equation:

 $P = 1.35 \text{ x } I_{F(AV)} + 0.096 \text{ x } I_{F}^{2}_{(RMS)}$ 

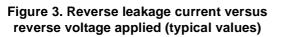
Symbol	Parameter	Test conditions	Тур.	Unit
Q <sub>cj</sub> <sup>(1)</sup>	Total capacitive charge	V <sub>R</sub> = 400 V	29.3	nC
C <sub>j</sub> Total capacita	Total capacitance	$V_{R} = 0 V, T_{c} = 25 °C, F = 1 MHz$	530	рF
	Total capacitance	$V_{R}$ = 300 V, T <sub>c</sub> = 25 °C, F = 1 MHz	55	μг

1. Most accurate value for the capacitive charge:  $Q_{cj} = \int_{0}^{V_{OUT}} c_{j}(v_R) dv_R$ 





#### Figure 1. Forward voltage drop versus forward Figure 2. Forward voltage drop versus forward current (typical values, low level)



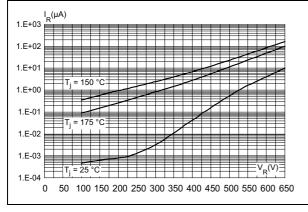
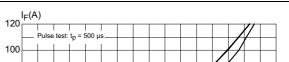


Figure 5. Junction capacitance versus reverse voltage applied (typical values)



current (typical values, high level)

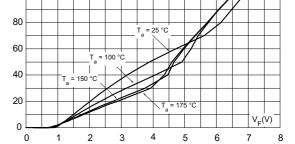
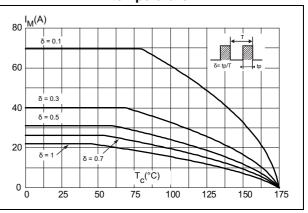
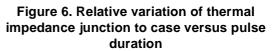


Figure 4. Peak forward current versus case temperature





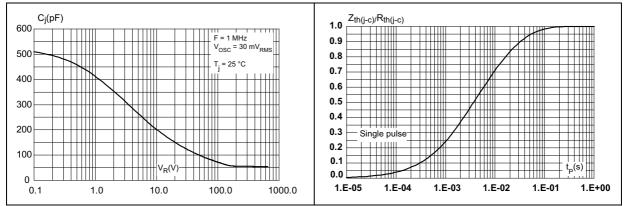
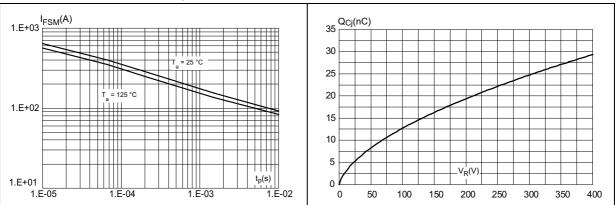




Figure 7. Non-repetitive peak surge forward current versus pulse duration (sinusoidal waveform)



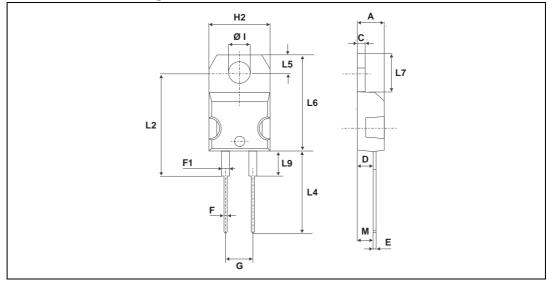
# Figure 8. Total capacitive charges versus reverse voltage applied (typical values)

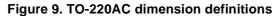


### 2 Package information

- Epoxy meets UL94, V0
- Recommended torque value (TO-220AC): 0.55 N·m
- Maximum torque value: 0.7 N·m for TO-220AC
- Cooling method: conduction (C)

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK<sup>®</sup> is an ST trademark.







		TO-220AC dimens			
	Dimensions				
Ref.	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
А	4.40	4.60	0.173	0.181	
С	1.23	1.32	0.048	0.051	
D	2.40	2.72	0.094	0.107	
E	0.49	0.70	0.019	0.027	
F	0.61	0.88	0.024 0.034		
F1	1.14 1.70 0.044		0.066		
G	4.95	4.95 5.15 0.194		0.202	
H2	10.00	10.40	0.393 0.409		
L2	16.4	0 typ.	0.645 typ.		
L4	13.00	14.00	0.511	0.551	
L5	2.65	2.95	0.104	0.116	
L6	15.25	15.75	0.600	0.620	
L7	6.20	6.60	0.244	0.259	
L9	3.50	3.93	0.137 0.154		
М	2.6	typ.	0.102 typ.		
Diam. I	3.75	3.85	0.147	0.151	

Table 6. TO-220AC dimension values



# **3** Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPSC12C065DY	PSC12C065DY	TO-220AC	1.86 g	50	Tube

## 4 Revision history

Table 8. Document revis	sion history
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Date	Revision	Changes
13-Jan-2015	1	First issue.



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